

L Number	Hits	Search Text	DB	Time stamp
1	1	(storage adj electrode) near10 above adj (semiconductor adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 13:12
2	3	(storage adj electrode) near10 above near10 (semiconductor adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 13:16
3	7	(semiconductor adj layer) near10 (gate adj insulating adj layer) near10 (storage adj capacitor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 13:14
4	0	(storage adj electrode) near10 on near10 (semiconductor adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 13:17
5	5	(storage adj electrode) adj (semiconductor adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 13:19
6	0	(auxiliary adj capacitor) adj (semiconductor adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 13:19
7	17	(auxiliary adj capacitor) near10 (semiconductor adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 13:23
8	0	(auxiliary adj capacitor adj electrode) near10 "on" near10 (semiconductor adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 13:24
9	0	(auxiliary adj capacitance adj electrode) near10 "on" near10 (semiconductor adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 13:24
10	0	(storage adj electrode) near10 "on" near10 (semiconductor adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 13:24
11	0	(storage adj electrode) near10 on near10 (semiconductor adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 13:25
12	3	(storage adj electrode) near10 above near10 (semiconductor adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 13:43
13	0	(pixel adj electrode) near10 contact near10 side near10 (storage adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 13:28
14	6	(pixel adj electrode) near10 side near10 (storage adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 13:29

15	39	(pixel adj electrode) near10 contact near10 (storage adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 13:39
16	0	(pixel adj electrode) near10 contact near10 (lateral adj side) near10 (storage adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 13:32
17	36	(storage adj electrode) near10 contact near10 (pixel adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 13:40
18	32	((pixel adj electrode) near10 contact near10 (storage adj electrode)) and ((storage adj electrode) near10 contact near10 (pixel adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 13:40
19	17	(pixel adj electrode) near10 connect near10 (storage adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 13:50
20	0	(pixel adj electrode) near10 connect near10 side near10 (storage adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 13:50
21	9	(pixel adj electrode) near10 adjacent near10 (storage adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 13:51
-	52	"349" and (liquid adj crystal adj seal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 15:53
-	120	(seal) near10 (display adj region)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 15:54
-	8	(seal) near10 (non-display adj region)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 15:54
-	125	(seal) near10 (passivation adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 16:06
-	0	((seal) near10 (display adj region)) and ((seal) near10 (non-display adj region)) and ((seal) near10 (passivation adj layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 15:55
-	1	((seal) near10 (display adj region)) and ((seal) near10 (passivation adj layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 15:55
-	0	(seal) near10 remove near10 (passivation adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 15:56

-	0	(seal) near10 (passivation adj layer) near10 remove	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 15:57
-	4768	"349" and (liquid adj crystal adj panel)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 16:09
-	9788	"349" and (seal or (seal adj region))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 16:13
-	1110	"349" and (display adj region)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 16:15
-	679	"349" and (passivation adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 16:16
-	1477	"349" and (protective adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 16:18
-	1	("349" and (liquid adj crystal adj panel)) and ("349" and (seal or (seal adj region))) and ("349" and (display adj region)) and ("349" and (passivation adj layer)) and ("349" and (protective adj layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 16:19
-	22	seal near10 (remov\$6) near10 ((protective or passivation) adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 16:37
-	1206	((349/153) or (349/190)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 16:27
-	2108	"349" and ((protective or passivation) adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 16:30
-	34	((((349/153) or (349/190)).CCLS.) and ("349" and ((protective or passivation) adj layer)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 16:30
-	387	seal near10 (remov\$6) near10 (protective or passivation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 16:50
-	1	seal near10 boundary near10 ((display and non-display) adj region)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 16:53
-	0	((passivation or protective) adj layer) near10 boundary near10 (display adj region)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 16:54

-	120	(seal) near10 (display adj region)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 16:57
-	8	(seal) near10 (non adj display adj region)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 16:58
-	8	((seal) near10 (display adj region)) and ((seal) near10 (non adj display adj region))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 17:00
-	2	seal near10 (boundary) near10 (display adj region)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 17:03
-	9	seal near10 (display adj region) near10 (non adj display adj region)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 17:15
-	0	((active and passivation) adj layer) near10 patterned near10 simulataneously	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 17:16
-	1	((active and passivation) adj layer) near10 patterned near10 simultaneously	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 17:17
-	3	((active and passivation) adj layer) near10 patterned	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 17:18
-	0	((active and passivation) adj layer) near10 mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 17:19
-	0	((active and protective) adj layer) near10 patterned	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 17:20
-	0	((active and protective) adj layer) near10 mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 17:20
-	3	((active and protective) adj layer) near10 pattern\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 17:22
-	0	((active and protective) adj layer) near10 pattern\$6 near10 together	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 17:24
-	0	((active and protective) adj layer) near10 formed near10 simultaneously	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 17:26

-	0	((active and protective) adj layer) near10 forming near10 simultaneously	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 17:27
-	0	(active and protective) near10 formed near10 simultaneously	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 17:28
-	0	(active and passivation) near10 formed near10 simultaneously	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 17:28
-	0	(active and passivation) near10 etch	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 17:29
-	9	(active and passivation) near10 mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 17:30
-	1152	(active and passivation) near10 layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 17:32
-	0	(active and passivation) near10 fabrication	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 17:32
-	237	(active and passivation) near10 formed	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 17:32
-	63	((active and passivation) near10 layer) and ((active and passivation) near10 formed)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 17:38
-	0	((active and passivation) adj layer) near10 (mask adj step)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 17:39
-	0	((active and passivation) adj layer) near10 (single adj mask adj step)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 17:40
-	0	(active and passivation) adj (film or layer) near10 pattern\$6 near10 together	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 17:43
-	4169	(active) near10 patterned	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 17:45
-	0	ha-young-hun.DID.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 17:46

-	1	ha-young-hun.in. and seal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 17:46
-	5	ha-young-hun.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 17:49
-	1	so-jae-moon.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 17:49
-	68	kim-jong-woo.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 17:49
-	7	((active and passivation) near10 etching)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 17:52
-	0	((active and passivation) near10 simultaneous near10 etching)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 17:52
-	0	((active and passivation) near10 simultaneous near10 etching)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/17 17:52
-	1	seal near10 periphery near10 display near10 non-display	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/18 09:38
-	4	seal near10 boundary near10 display near10 non-display	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/18 09:46
-	7	(patterning) near10 ((active and passivation) adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/18 09:55
-	2	5621553.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/18 09:59
-	89	(second adj substrate) near10 (color adj filter) near10 (common adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/18 10:07
-	22	(gate adj insulating adj layer) near10 (thin adj film adj transistor) near10 (passivation adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/18 10:13
-	1	((second adj substrate) near10 (color adj filter) near10 (common adj electrode)) and ((gate adj insulating adj layer) near10 (thin adj film adj transistor) near10 (passivation adj layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/18 10:10

-	0	(gate adj insulating adj layer) near10 on near10 (gate adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/18 10:14
-	413	(gate adj insulating adj layer) near10 over near10 (gate adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/18 10:16
-	0	(thin adj film adj transistor) near10 on near10 (gate adj insulating adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/18 10:17
-	30	(thin adj film adj transistor) near10 over near10 (gate adj insulating adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/18 10:18
-	0	(pixel adj electrode) near10 connect near10(thin adj film adj transistor) near10 over near10 (gate adj insulating adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/18 10:18
-	1149	(pixel adj electrode) near10 connected near10 (thin adj film adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/18 10:20
-	54	(passivation adj layer) near10 over near10 (thin adj film adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/18 10:21
-	0	((gate adj insulating adj layer) near10 over near10 (gate adj electrode)) and ((thin adj film adj transistor) near10 over near10 (gate adj insulating adj layer)) and ((pixel adj electrode) near10 connected near10 (thin adj film adj transistor)) and ((passivation adj layer) near10 over near10 (thin adj film adj transistor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/18 10:21
-	11	((pixel adj electrode) near10 connected near10 (thin adj film adj transistor)) and ((passivation adj layer) near10 over near10 (thin adj film adj transistor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/18 10:26
-	1	((gate adj insulating adj layer) near10 over near10 (gate adj electrode)) and ((thin adj film adj transistor) near10 over near10 (gate adj insulating adj layer)) and ((pixel adj electrode) near10 connected near10 (thin adj film adj transistor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/18 10:22
-	0	(gate adj electrode) near10 (gate adj insulating adj layer) near10 (thin adj field adj transistor) near10 pixel near10 (passivation adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/18 10:28
-	1	(seal) near10 (screen adj printing) near10 (thermosetting adj resin) near10 (glass adj fiber)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/18 10:51
-	114	(screen adj printing) near10 (thermosetting adj resin)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/18 10:51

-	826	(thermosetting adj resin) near10 (glass adj fiber)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/18 10:55
-	5	((screen adj printing) near10 (thermosetting adj resin)) and ((thermosetting adj resin) near10 (glass adj fiber))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/18 11:09
-	1	(seal) near10 (data adj pad) near10 (data adj line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/18 17:24
-	2	(seal) near10 (data adj pad)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/18 17:26
-	1	(seal) near10 between near10 (data adj pad)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/18 17:29
-	9802	"349" and seal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/18 17:34
-	152	"349" and (data adj pad)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/18 17:35
-	2130	"349" and (data adj line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/18 17:37
-	12	("349" and seal) and ("349" and (data adj pad)) and ("349" and (data adj line))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/18 17:47
-	1	(data adj pad) near10 seal near10 (data adj line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/18 17:49
-	19	(seal adj pattern) near10 data	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 09:20
-	0	(seal adj pattern) near10 (signal adj pad)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 09:21
-	19	(seal adj pattern) near10 (signal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 09:30
-	1	seal adj pattern adj forming adj region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 09:32

-	1	(seal adj pattern) near10 (forming adj region)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 09:33
-	1	(seal adj pattern) near10 (formation adj region)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 09:34
-	11	sealant adj formation adj area	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 09:45
-	2567	(seal or sealant) near10 forming near10 (area or region)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 09:51
-	0	(gate adj line) near10 ((gate and capacitance) adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 09:53
-	6	(gate adj line) near10 ((gate and capacitor) adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 11:26
-	865	(data adj line) near10 (drain adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 10:00
-	6	((gate adj line) near10 ((gate and capacitor) adj electrode)) and ((data adj line) near10 (drain adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 10:02
-	256	(source adj electrode) near10 apart near10 (drain adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 10:04
-	71	(pixel adj electrode) near10 connect near10 (source adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 11:00
-	23	(pixel adj electrode) near10 over near10 (capacitor adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 10:12
-	0	((source adj electrode) near10 apart near10 (drain adj electrode)) and ((pixel adj electrode) near10 connect near10 (source adj electrode)) and ((pixel adj electrode) near10 over near10 (capacitor adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 10:09
-	1	((source adj electrode) near10 apart near10 (drain adj electrode)) and ((pixel adj electrode) near10 connect near10 (source adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 10:09
-	0	((pixel adj electrode) near10 connect near10 (source adj electrode)) and ((pixel adj electrode) near10 over near10 (capacitor adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 10:09

-	17	(pixel adj electrode) near10 overlap near10 (capacitor adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 10:23
-	0	((pixel adj electrode) near10 connect near10 (source adj electrode)) and ((pixel adj electrode) near10 overlap near10 (capacitor adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 10:14
-	123	(semiconductor adj layer) near10 formed near10 under near10 (gate adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 10:26
-	0	(semiconductor adj layer) near10 formed near10 under near10 (thin adj field adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 10:27
-	75	(semiconductor adj layer) near10 formed near10 under near10 (transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 10:29
-	18	((semiconductor adj layer) near10 formed near10 under near10 (gate adj electrode)) and ((semiconductor adj layer) near10 formed near10 under near10 (transistor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 10:39
-	44	(auxiliary adj (capacitance or capacitor) adj electrode) near10 between near10 (capacitance or capacitor) and pixel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 10:47
-	3	(auxiliary adj (capacitor or capacitance) adj electrode) near10 connect near10 (pixel adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 11:10
-	0	((auxiliary adj (capacitance or capacitor) adj electrode) near10 between near10 (capacitance or capacitor) and pixel) and ((auxiliary adj (capacitor or capacitance) adj electrode) near10 connect near10 (pixel adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 10:49
-	0	((pixel adj electrode) near10 connect near10 (source adj electrode)) and ((auxiliary adj (capacitance or capacitor) adj electrode) near10 between near10 (capacitance or capacitor) and pixel)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 10:59
-	2	5629787.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 11:10
-	1	(gate adj insulating adj layer) near10 formed near10 (display adj (area or region))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 11:29
-	10	(gate adj insulating adj layer) near10 (display adj (area or region))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 11:46
-	1	(gate adj insulating adj layer) near10 between near10(display adj (area or region))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 11:38

-	1	(gate adj insulating adj layer) near10 boundary near10 (display adj (area or region))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 11:39
-	8	(alignment) near10 (rubbing) near10 spacer near10 seal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 11:50
-	0	seal near10 formed near10 over near10 (gate adj insulating adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 11:52
-	0	seal near10 formed near10 on near10 (gate adj insulating adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 11:53
-	1	seal near10 over near10 (gate adj insulating adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 11:54
-	12	auxiliary near10 over near10 (semiconductor adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 16:10
-	0	(auxiliary adj (capacitor or capacitance)) adj electrode near10 over near10 (semiconductor adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 16:12
-	0	(auxiliary adj (capacitor or capacitance)) adj electrode near10 above near10 (semiconductor adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 16:12
-	6	(auxiliary adj (capacitor or capacitance)) adj electrode near10 (semiconductor adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 16:14
-	658	(semiconductor adj layer) near10 formed near10 (gate adj insulating adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 16:16
-	0	((auxiliary adj (capacitor or capacitance)) adj electrode near10 (semiconductor adj layer)) and ((semiconductor adj layer) near10 formed near10 (gate adj insulating adj layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 16:17
-	2	(passivation adj layer) near10 (auxiliary adj (capacitance or capacitor)) adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 16:21
-	0	(protective adj layer) near10 (auxiliary adj (capacitance or capacitor)) adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 16:21
-	0	(protection adj layer) near10 (auxiliary adj (capacitance or capacitor)) adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 16:22

-	1	(passivation adj layer) near (auxiliary adj (capacitance or capacitor)) adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 16:22
-	3	(passivation adj layer) near (storage adj (capacitance or capacitor)) adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 16:26
-	1	(pixel adj electrode) near side near (storage adj (capacitance or capacitor)) adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 16:28
-	1	(pixel adj electrode) near adjacent near (storage adj (capacitance or capacitor)) adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 16:29
-	0	(pixel adj electrode) near contacting near (storage adj (capacitance or capacitor)) adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 16:29
-	0	(seal) near10 for near10 ((cell or substrate) adj (spacing or gap)) near10 bonding	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 09:05
-	3	(seal) near10 ((cell or substrate) adj (spacing or gap)) near10 bonding	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/20 09:05